Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Leadless ultra small and ultra thin SMD plastic package: 1.1 × 1.0 × 0.37 mm
- Exposed drain pad for excellent thermal conduction
- ElectroStatic Discharge (ESD) protection 1.5 kV HBM
- Drain-source on-state resistance R_{DSon} = 69 mΩ
- Very low gate-source threshold voltage for portable applications V_{GS(th)} = -0.68 V

3. Applications

- High-side load switch and charging switch for portable devices
- Power management in battery driven portables
- LED driver
- DC-to-DC converter

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V_{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-	-2.9	Α
Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -2.9 A; T_j = 25 °C		_	69	85	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		D I
2	S	source		
3	D	drain	4 3	G T
4	D	drain	2	¥ FI
			Transparent top view DFN1010D-3 (SOT1215)	S 017aaa259

6. Ordering information

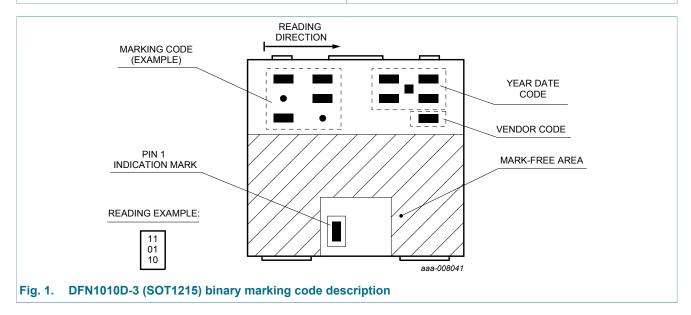
Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMXB75UPE	DFN1010D-3	DFN1010D-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 1.1 x 1.0 x 0.37 mm	SOT1215		

7. Marking

Table 4. Marking codes

Type number	Marking code
PMXB75UPE	00 01 00



PMXB75UPE

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V_{GS}	gate-source voltage			-8	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-2.9	Α
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-1.9	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-12	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	317	mW
			[1]	-	1070	mW
		T _{sp} = 25 °C		-	8330	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-dra	in diode				'	,
I _S	source current	T _{amb} = 25 °C	[1]	-	-1	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

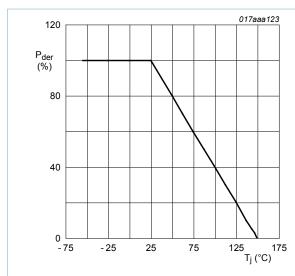


Fig. 2. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

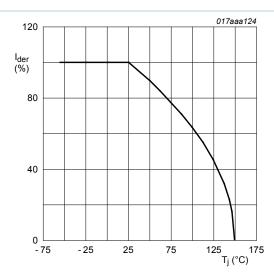


Fig. 3. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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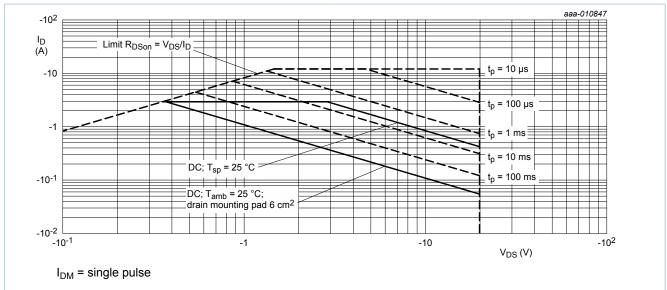


Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
f	thermal resistance in free air from junction to ambient	in free air	[1]	-	271	312	K/W
			[2]	-	102	117	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	10	15	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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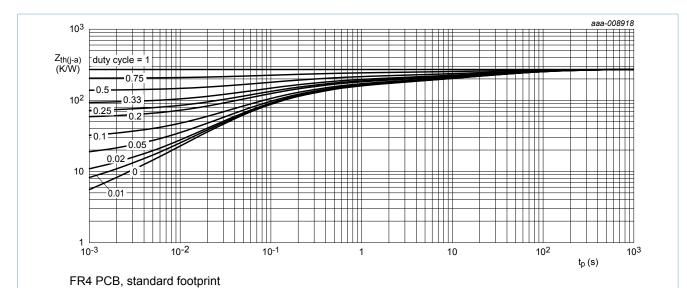
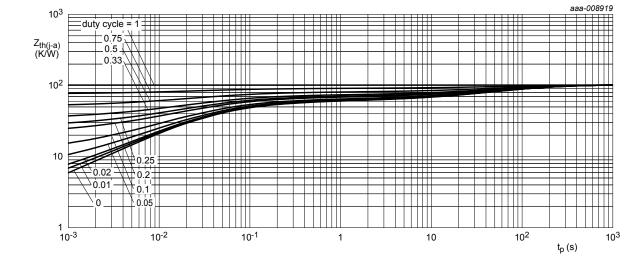


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain $6\ \mathrm{cm}^2$

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = -250 μ A; V_{GS} = 0 V; T_j = 25 °C	-20	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = -250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C	-0.4	-0.68	-1	V
I _{DSS}	drain leakage current	V _{DS} = -20 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μA
I _{GSS}	gate leakage current	V_{GS} = -8 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-10	μΑ
		V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-1	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μΑ
R _{DSon}	drain-source on-state	V_{GS} = -4.5 V; I_D = -2.9 A; T_j = 25 °C	-	69	85	mΩ
	resistance	V _{GS} = -4.5 V; I _D = -2.9 A; T _j = 150 °C	-	99	122	mΩ
		V_{GS} = -2.5 V; I_D = -2.6 A; T_j = 25 °C	-	86	110	mΩ
		V_{GS} = -1.8 V; I_D = -0.4 A; T_j = 25 °C	-	130	200	mΩ
		V_{GS} = -1.5 V; I_D = -50 mA; T_j = 25 °C	-	205	450	mΩ
	V_{GS} = -1.2 V; I_D = -10 mA; T_j = 25 °C	-	950	-	mΩ	
9fs	forward transconductance	V_{DS} = -10 V; I_D = -2 A; T_j = 25 °C	-	8.4	-	S
R_G	gate resistance	f = 1 MHz	-	11.3	-	Ω
Dynamic ch	naracteristics		'			
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I_{D} = -2.9 A; V_{GS} = -4.5 V;	-	6.8	12	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.9	-	nC
Q_{GD}	gate-drain charge		-	2.1	-	nC
C _{iss}	input capacitance	V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V;	-	608	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	75	-	pF
C _{rss}	reverse transfer capacitance		-	64	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I_{D} = -2.9 A; V_{GS} = -4.5 V;	-	6	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 °C$	-	19	-	ns
$t_{d(off)}$	turn-off delay time		-	29	-	ns
t _f	fall time		-	15	-	ns
Source-drai	in diode					
V_{SD}	source-drain voltage	I _S = -1 A; V _{GS} = 0 V; T _j = 25 °C	-	-0.7	-1.2	V
	and the second s			100		1

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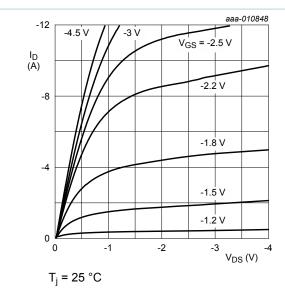


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values

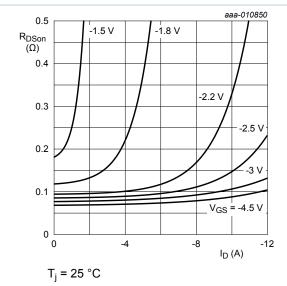


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

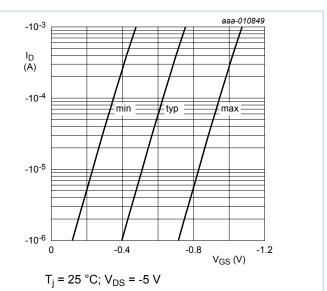


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

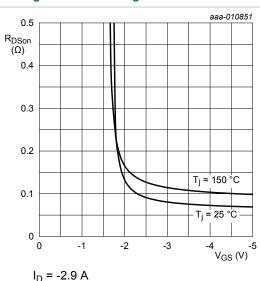


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

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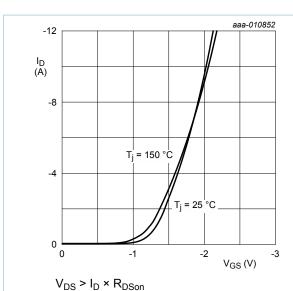


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

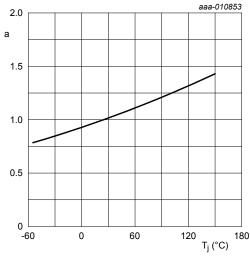


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

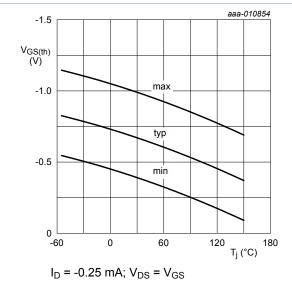


Fig. 13. Gate-source threshold voltage as a function of junction temperature

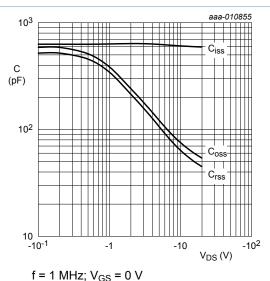


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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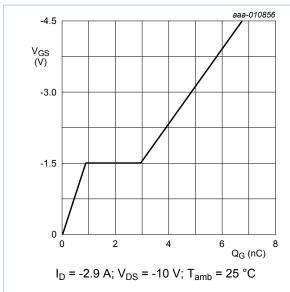


Fig. 15. Gate-source voltage as a function of gate charge; typical values

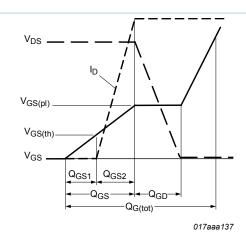


Fig. 16. MOSFET transistor: Gate charge waveform definitions

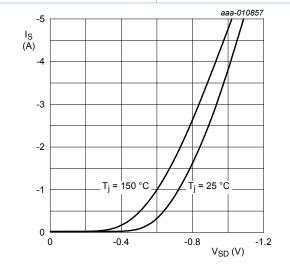
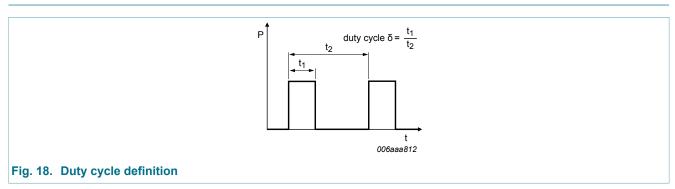


Fig. 17. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



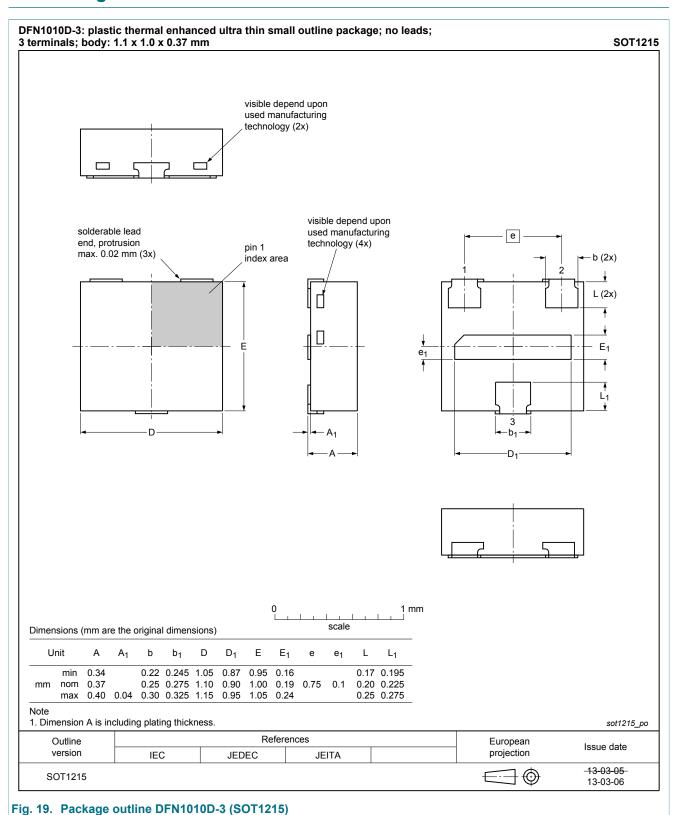
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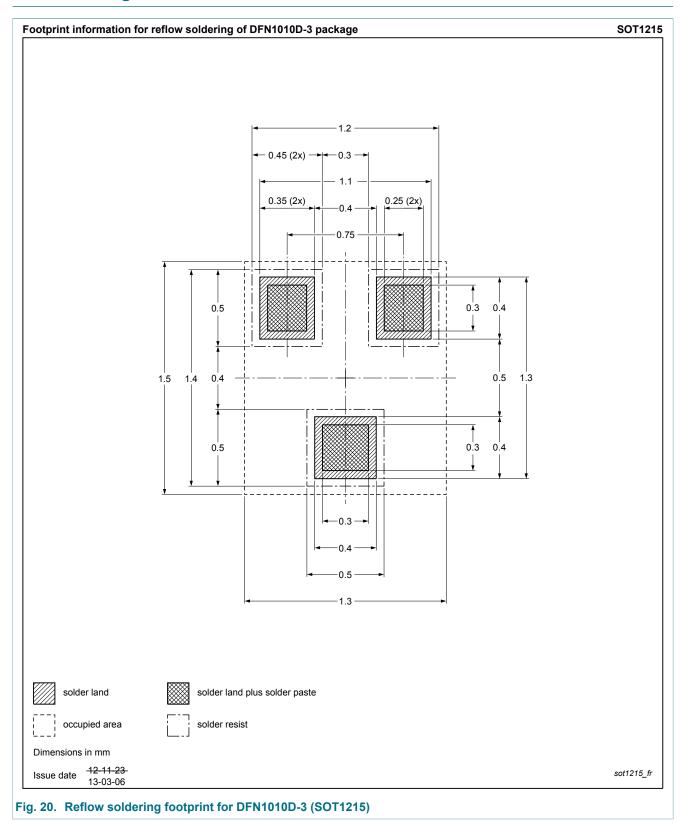
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMXB75UPE v.3	20140708	Product data sheet	-	PMXB75UPE v.2
Modifications:	 Product status char 	nged		
PMXB75UPE v.2	20140218	Preliminary data sheet	-	PMXB75UPE v.1
PMXB75UPE v.1	20140204	Preliminary data sheet	-	-

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Document status [1][2]	Product status [3]	Definition
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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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